

**Preliminary datasheet**  
**62 mm C-Series module with CoolSiC™ Trench MOSFET**

**Features**

- Electrical features
  - $V_{DSS} = 1200\text{ V}$
  - $I_{DN} = 180\text{ A} / I_{DRM} = 360\text{ A}$
  - High current density
  - Low switching losses
- Mechanical features
  - 4 kV AC 1 min insulation

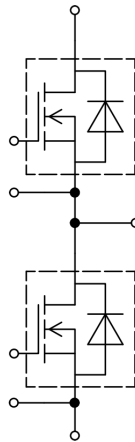
**Potential applications**

- UPS systems
- Solar applications
- DC/DC converter
- High-frequency switching application
- Energy storage systems
- DC charger for EV

**Product validation**

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

**Description**



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## 1 Package

**Table 1** Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	$V_{ISOL}$	RMS, $f = 50 \text{ Hz}$ , $t = 60 \text{ s}$	4.0	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	$Al_2O_3$	
Creepage distance	$d_{Creep}$	terminal to heatsink	29.0	mm
Creepage distance	$d_{Creep}$	terminal to terminal	23.0	mm
Clearance	$d_{Clear}$	terminal to heatsink	23.0	mm
Clearance	$d_{Clear}$	terminal to terminal	11.0	mm
Comparative tracking index	$CTI$		> 400	
Relative thermal index (electrical)	$RTI$	housing	140	°C

**Table 2** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	$L_{sCE}$			20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25 \text{ °C}$ , per switch		0.47		mΩ
Storage temperature	$T_{stg}$		-40		125	°C
Mounting torque for module mounting	$M$	- Mounting according to valid application note	M6, Screw	3	6	Nm
Terminal connection torque	$M$	- Mounting according to valid application note	M6, Screw	2.5	5	Nm
Weight	$G$			340		g

## 2 MOSFET

**Table 3** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage	$V_{DSS}$	$T_{vj} = 25 \text{ °C}$	1200	V
Implemented drain current	$I_{DN}$		180	A
Continuous DC drain current	$I_{DDC}$	$T_{vj} = 175 \text{ °C}$ , $V_{GS} = 18 \text{ V}$ $T_C = 115 \text{ °C}$	140	A
Repetitive peak drain current	$I_{DRM}$	verified by design, $t_p$ limited by $T_{vjmax}$	360	A

(table continues...)

**Table 3 (continued) Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Gate-source voltage, max. transient voltage	$V_{GS}$	$D < 0.01$	-10/23	V
Gate-source voltage, max. static voltage	$V_{GS}$		-7/20	V

**Table 4 Recommended values**

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

**Table 5 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source on-resistance	$R_{DS(on)}$	$I_D = 180\text{ A}$	$V_{GS} = 18\text{ V}$ , $T_{vj} = 25\text{ °C}$		5.5		mΩ
			$V_{GS} = 18\text{ V}$ , $T_{vj} = 125\text{ °C}$		8.9		
			$V_{GS} = 18\text{ V}$ , $T_{vj} = 175\text{ °C}$		11.8		
			$V_{GS} = 15\text{ V}$ , $T_{vj} = 25\text{ °C}$		6.6		
Gate threshold voltage	$V_{GS(th)}$	$I_D = 60\text{ mA}$ , $V_{DS} = V_{GS}$ , $T_{vj} = 25\text{ °C}$ , (tested after 1ms pulse at $V_{GS} = +20\text{ V}$ )	3.45	4.3	5.15	V	
Total gate charge	$Q_G$	$V_{DD} = 800\text{ V}$ , $V_{GS} = -3/18\text{ V}$		0.446		μC	
Internal gate resistor	$R_{Gint}$	$T_{vj} = 25\text{ °C}$		1.4		Ω	
Input capacitance	$C_{ISS}$	$f = 100\text{ kHz}$ , $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$		13.2		nF	
Output capacitance	$C_{OSS}$	$f = 100\text{ kHz}$ , $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$		0.63		nF	
Reverse transfer capacitance	$C_{rSS}$	$f = 100\text{ kHz}$ , $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$		0.042		nF	
$C_{OSS}$ stored energy	$E_{OSS}$	$V_{DS} = 800\text{ V}$ , $V_{GS} = -3/18\text{ V}$ , $T_{vj} = 25\text{ °C}$		258		μJ	
Drain-source leakage current	$I_{DSS}$	$V_{DS} = 1200\text{ V}$ , $V_{GS} = -3\text{ V}$		0.09	527	μA	
Gate-source leakage current	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $T_{vj} = 25\text{ °C}$	$V_{GS} = 20\text{ V}$		400	nA	

**(table continues...)**

**Table 5 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time (inductive load)	$t_{d\ on}$	$I_D = 180\ A, R_{Gon} = 3.9\ \Omega, V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	60		ns
			$T_{vj} = 125\ ^\circ C$	58		
			$T_{vj} = 175\ ^\circ C$	58		
Rise time (inductive load)	$t_r$	$I_D = 180\ A, R_{Gon} = 3.9\ \Omega, V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	59		ns
			$T_{vj} = 125\ ^\circ C$	59		
			$T_{vj} = 175\ ^\circ C$	61		
Turn-off delay time (inductive load)	$t_{d\ off}$	$I_D = 180\ A, R_{Goff} = 3.6\ \Omega, V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	101		ns
			$T_{vj} = 125\ ^\circ C$	108		
			$T_{vj} = 175\ ^\circ C$	111		
Fall time (inductive load)	$t_f$	$I_D = 180\ A, R_{Goff} = 3.6\ \Omega, V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	29		ns
			$T_{vj} = 125\ ^\circ C$	29		
			$T_{vj} = 175\ ^\circ C$	29		
Turn-on energy loss per pulse	$E_{on}$	$I_D = 180\ A, V_{DD} = 600\ V, L_\sigma = 10\ nH, V_{GS} = -3/18\ V, R_{Gon} = 3.9\ \Omega, di/dt = 5.5\ kA/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	2.8		mJ
			$T_{vj} = 125\ ^\circ C$	3.2		
			$T_{vj} = 175\ ^\circ C$	3.6		
Turn-off energy loss per pulse	$E_{off}$	$I_D = 180\ A, V_{DD} = 600\ V, L_\sigma = 10\ nH, V_{GS} = -3/18\ V, R_{Goff} = 3.6\ \Omega, dv/dt = 16.6\ kV/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	2.9		mJ
			$T_{vj} = 125\ ^\circ C$	3.1		
			$T_{vj} = 175\ ^\circ C$	3.3		
Thermal resistance, junction to case	$R_{thJC}$	per MOSFET			0.188	K/W
Thermal resistance, case to heat sink	$R_{thCH}$	per MOSFET, $\lambda_{grease} = 1\ W/(m\cdot K)$		0.0420		K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		175	$^\circ C$

**Note:** The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.

$T_{vj,op} > 150\ ^\circ C$  is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13.

### 3 Body diode (MOSFET)

**Table 6** Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	$I_{SD}$	$T_{vj} = 175\text{ °C}$ , $V_{GS} = -3\text{ V}$	$T_C = 115\text{ °C}$	75	A

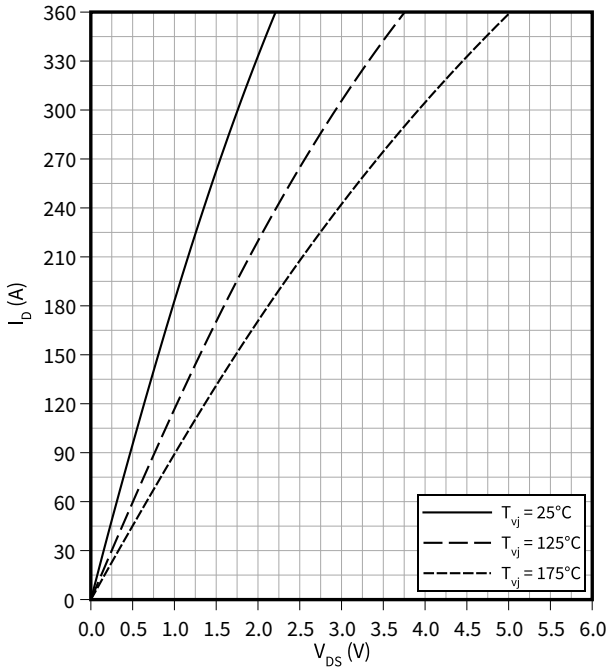
**Table 7** Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	$V_{SD}$	$I_{SD} = 180\text{ A}$ , $V_{GS} = -3\text{ V}$	$T_{vj} = 25\text{ °C}$		4.35	5.75	V
			$T_{vj} = 125\text{ °C}$		4.05		
			$T_{vj} = 175\text{ °C}$		3.95		

## 4 Characteristics diagrams

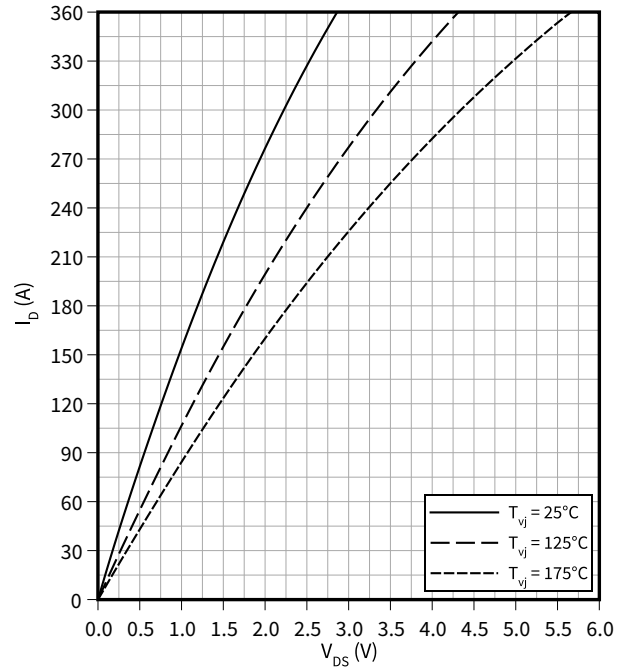
**Output characteristic (typical), MOSFET**

$I_D = f(V_{DS})$   
 $V_{GS} = 18\text{ V}$



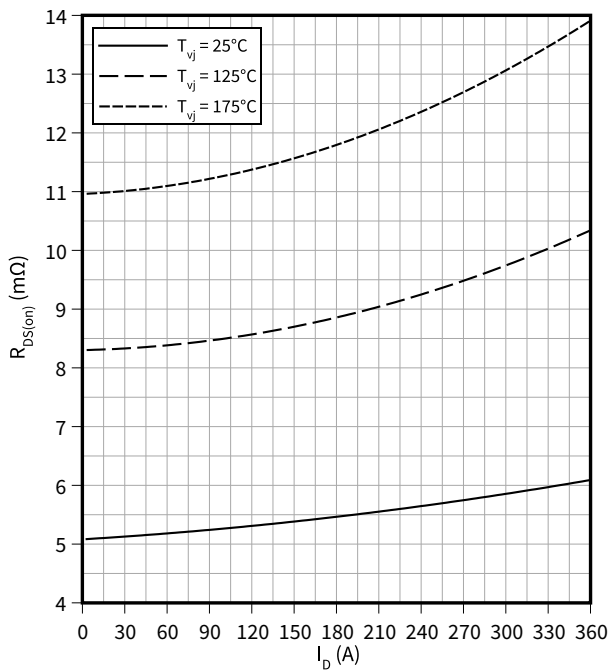
**Output characteristic (typical), MOSFET**

$I_D = f(V_{DS})$   
 $V_{GS} = 15\text{ V}$



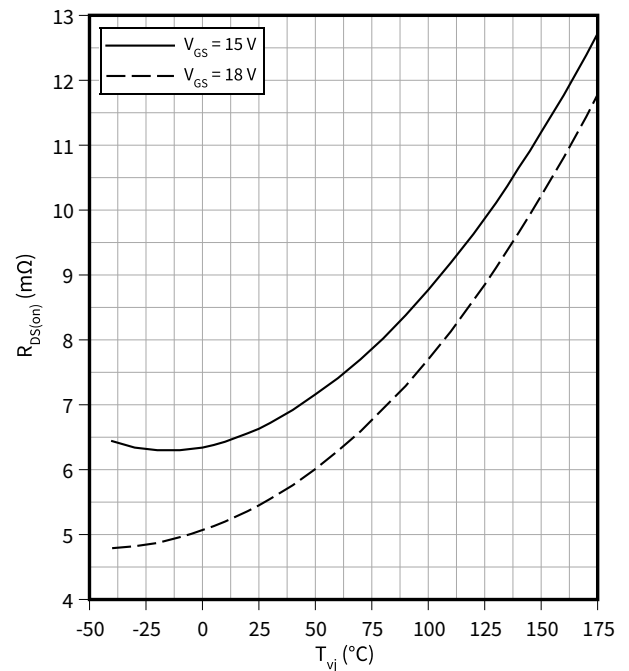
**Drain source on-resistance (typical), MOSFET**

$R_{DS(on)} = f(I_D)$   
 $V_{GS} = 18\text{ V}$



**Drain source on-resistance (typical), MOSFET**

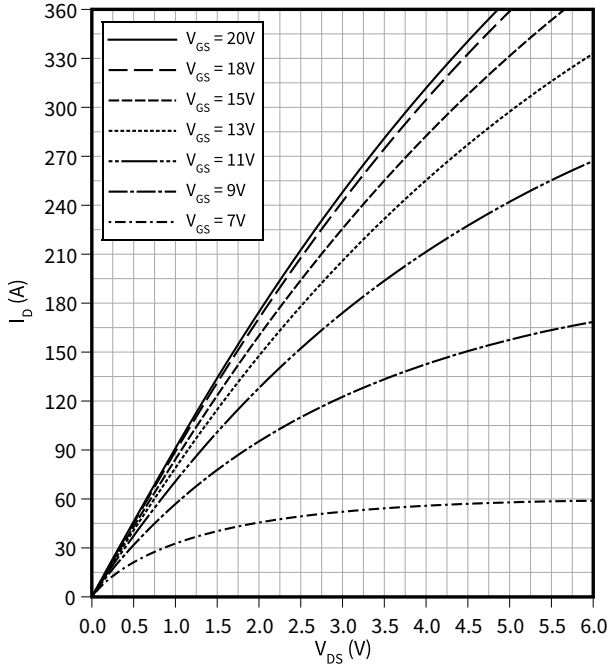
$R_{DS(on)} = f(T_{vj})$   
 $I_D = 180\text{ A}$



4 Characteristics diagrams

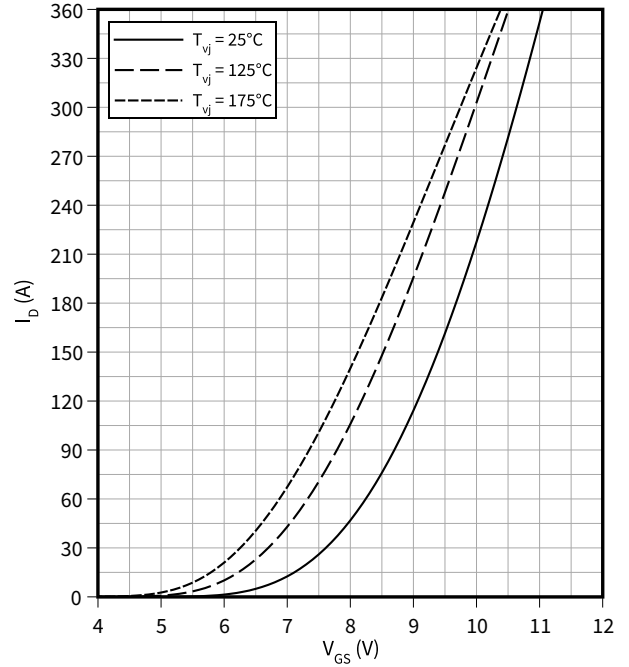
**Output characteristic field (typical), MOSFET**

$I_D = f(V_{DS})$   
 $T_{vj} = 175\text{ °C}$



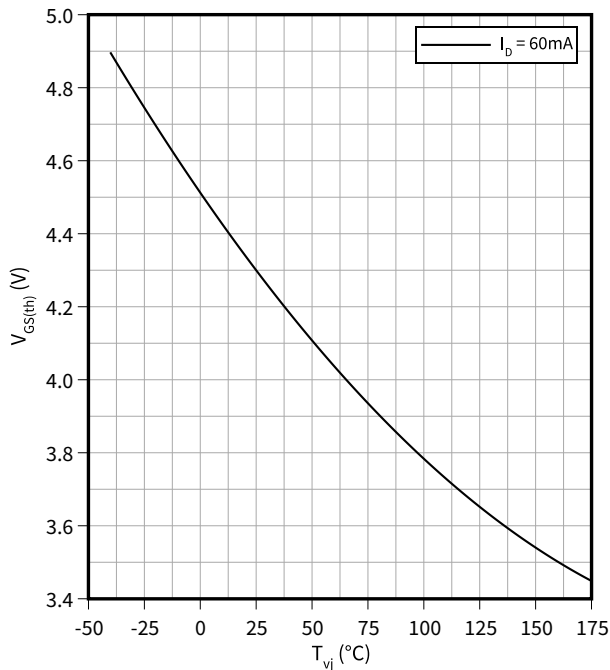
**Transfer characteristic (typical), MOSFET**

$I_D = f(V_{GS})$   
 $V_{DS} = 20\text{ V}$



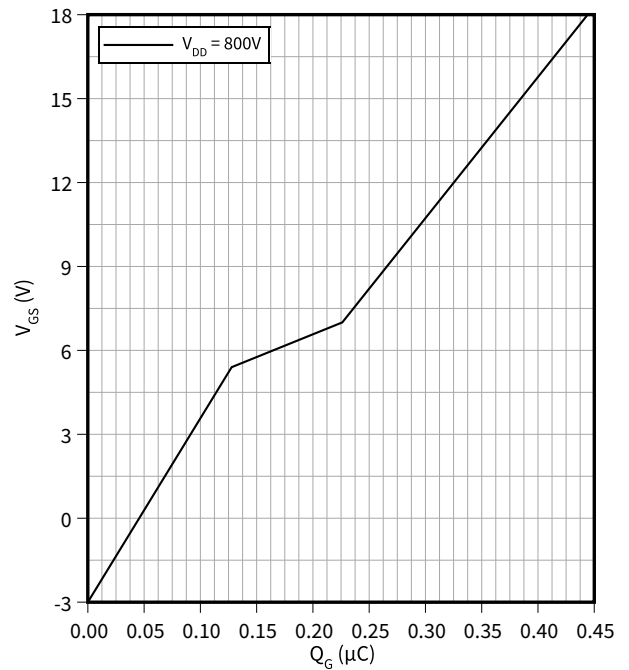
**Gate-source threshold voltage (typical), MOSFET**

$V_{GS(th)} = f(T_{vj})$   
 $V_{GS} = V_{DS}$



**Gate charge characteristic (typical), MOSFET**

$V_{GS} = f(Q_G)$   
 $I_D = 180\text{ A}, T_{vj} = 25\text{ °C}$

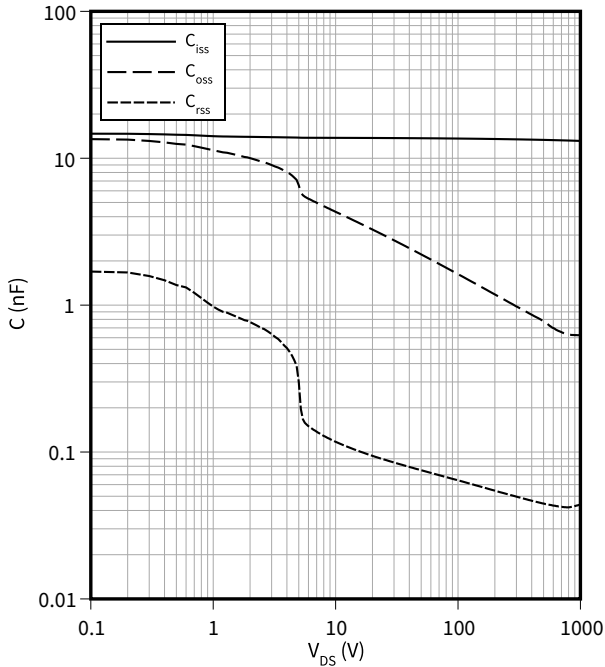




4 Characteristics diagrams

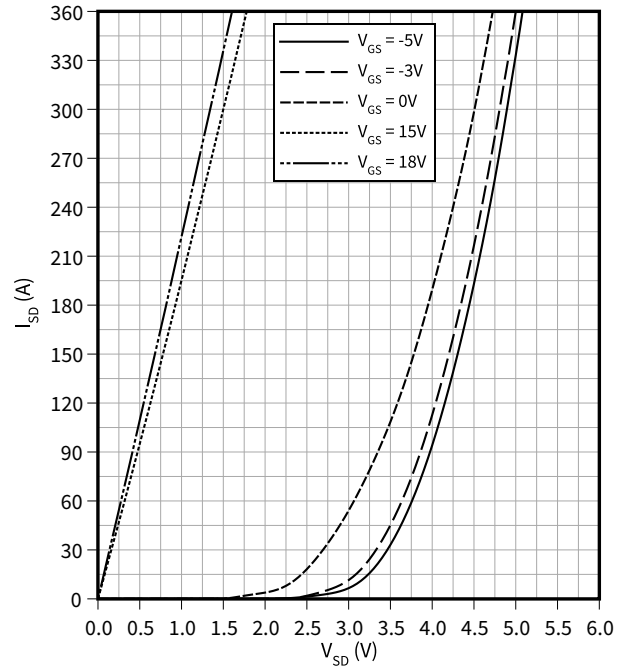
**Capacity characteristic (typical), MOSFET**

$C = f(V_{DS})$   
 $f = 100 \text{ kHz}, T_{vj} = 25 \text{ }^\circ\text{C}, V_{GS} = 0 \text{ V}$



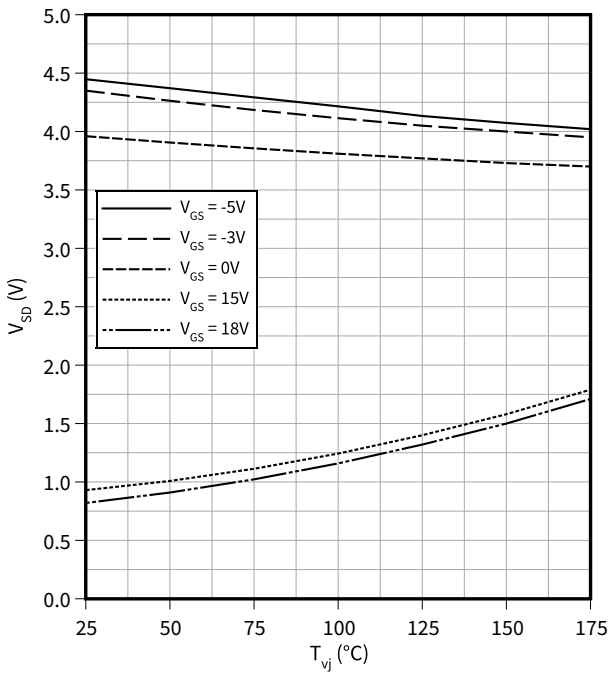
**Forward characteristic body diode (typical), MOSFET**

$I_{SD} = f(V_{SD})$   
 $T_{vj} = 25 \text{ }^\circ\text{C}$



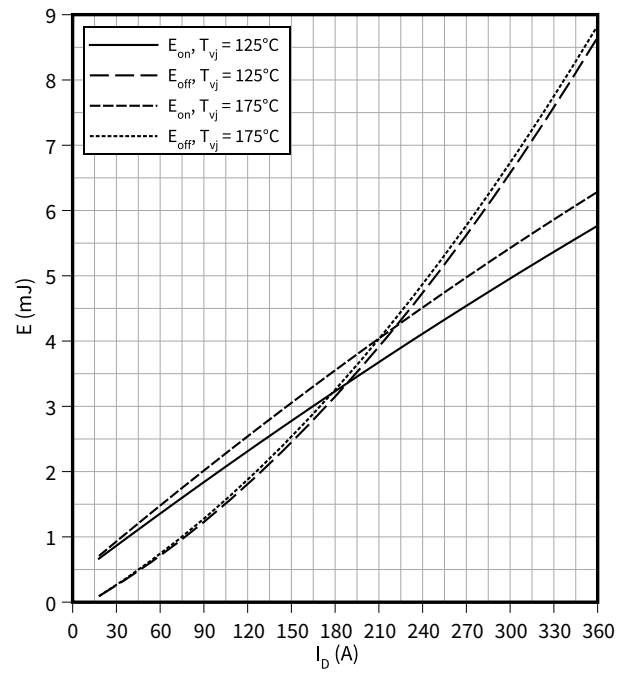
**Forward voltage of body diode (typical), MOSFET**

$V_{SD} = f(T_{vj})$   
 $I_{SD} = 180 \text{ A}$



**Switching losses (typical), MOSFET**

$E = f(I_D)$   
 $R_{Goff} = 3.6 \text{ } \Omega, R_{Gon} = 3.9 \text{ } \Omega, V_{DD} = 600 \text{ V}, V_{GS} = -3/18 \text{ V}$

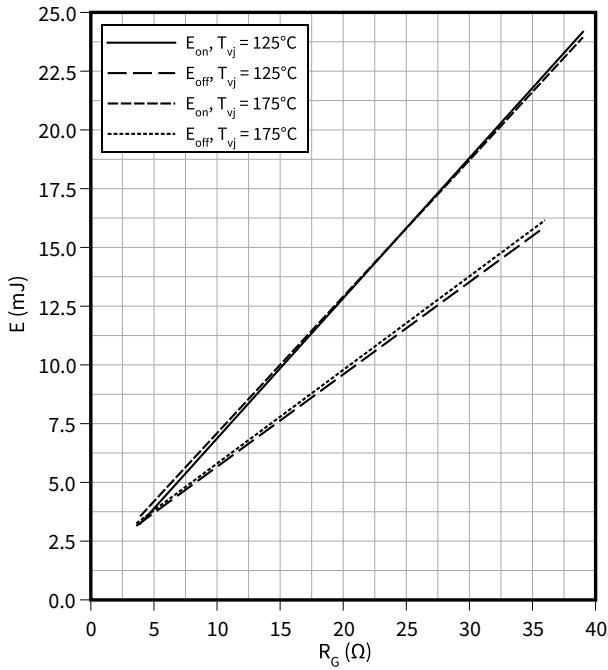


4 Characteristics diagrams

**Switching losses (typical), MOSFET**

$E = f(R_G)$

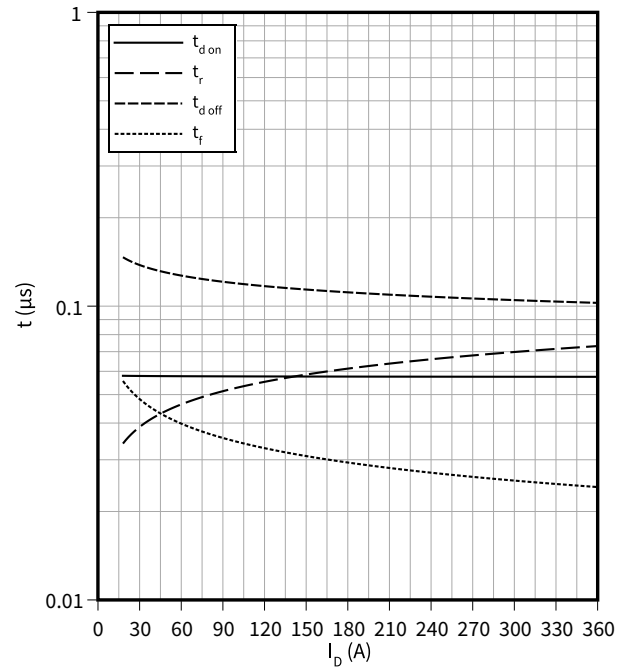
$V_{DD} = 600\text{ V}, I_D = 180\text{ A}, V_{GS} = -3/18\text{ V}$



**Switching times (typical), MOSFET**

$t = f(I_D)$

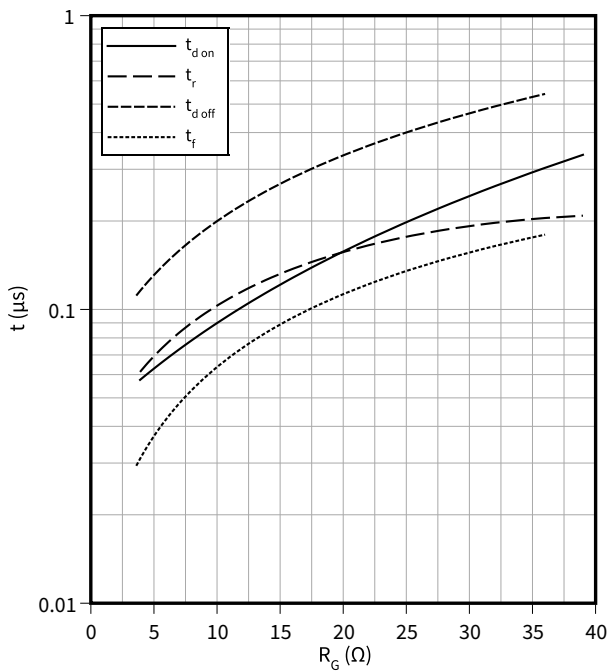
$R_{Goff} = 3.6\ \Omega, R_{Gon} = 3.9\ \Omega, V_{DD} = 600\text{ V}, T_{vj} = 175\text{ }^\circ\text{C}, V_{GS} = -3/18\text{ V}$



**Switching times (typical), MOSFET**

$t = f(R_G)$

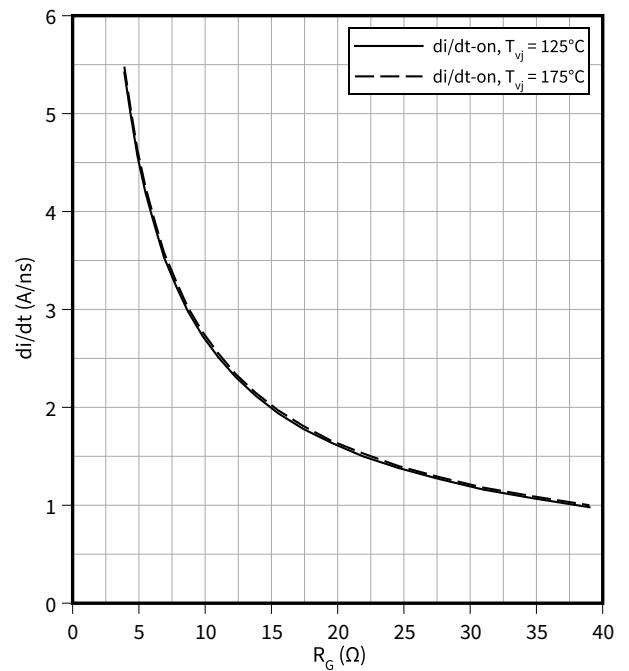
$V_{DD} = 600\text{ V}, I_D = 180\text{ A}, T_{vj} = 175\text{ }^\circ\text{C}, V_{GS} = -3/18\text{ V}$



**Current slope (typical), MOSFET**

$di/dt = f(R_G)$

$V_{DD} = 600\text{ V}, I_D = 180\text{ A}, V_{GS} = -3/18\text{ V}$

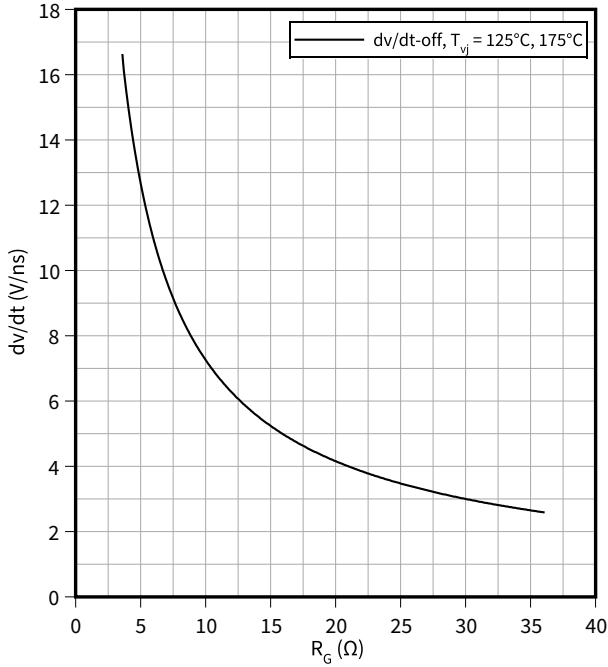


4 Characteristics diagrams

**Voltage slope (typical), MOSFET**

$dv/dt = f(R_G)$

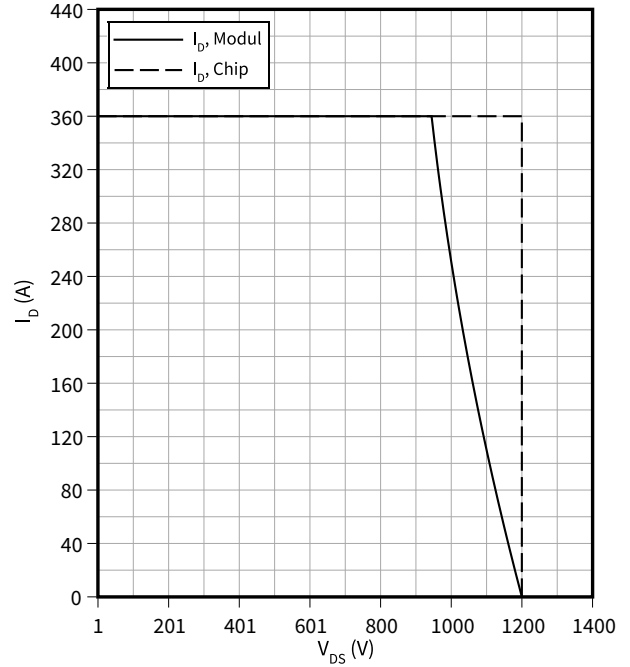
$V_{DD} = 600\text{ V}, I_D = 180\text{ A}, V_{GS} = -3/18\text{ V}$



**Reverse bias safe operating area (RBSOA), MOSFET**

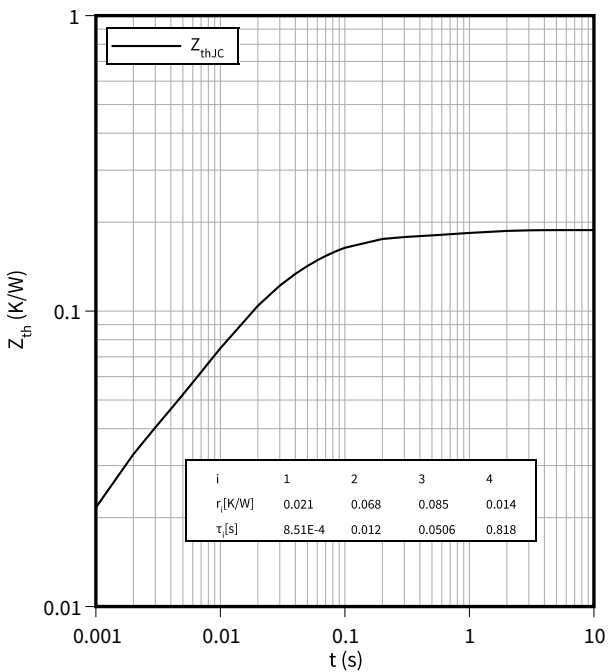
$I_D = f(V_{DS})$

$R_{Goff} = 3.6\ \Omega, T_{vj} = 175\ \text{°C}, V_{GS} = -3/18\text{ V}$



**Transient thermal impedance, MOSFET**

$Z_{th} = f(t)$



## 5 Circuit diagram

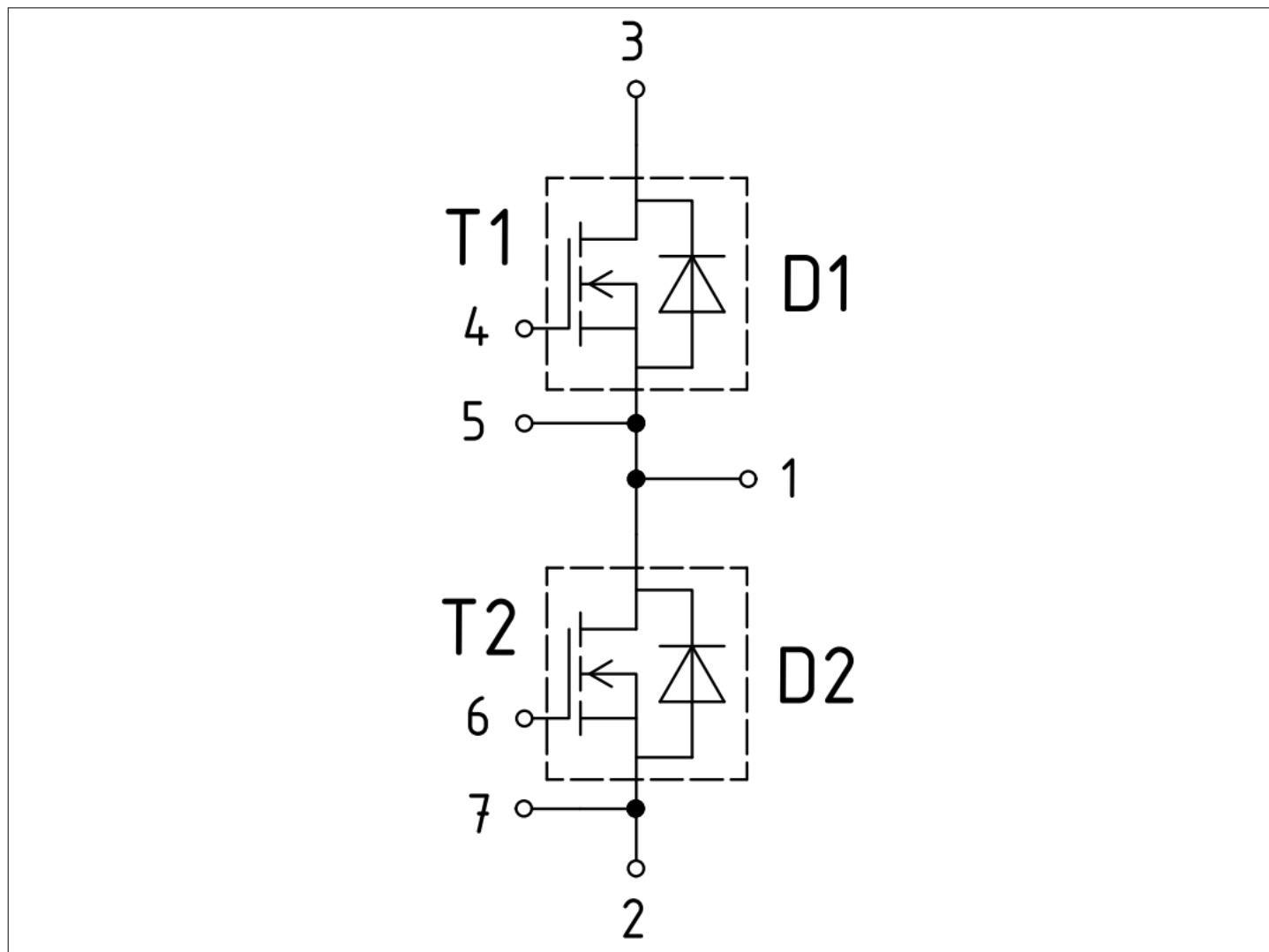
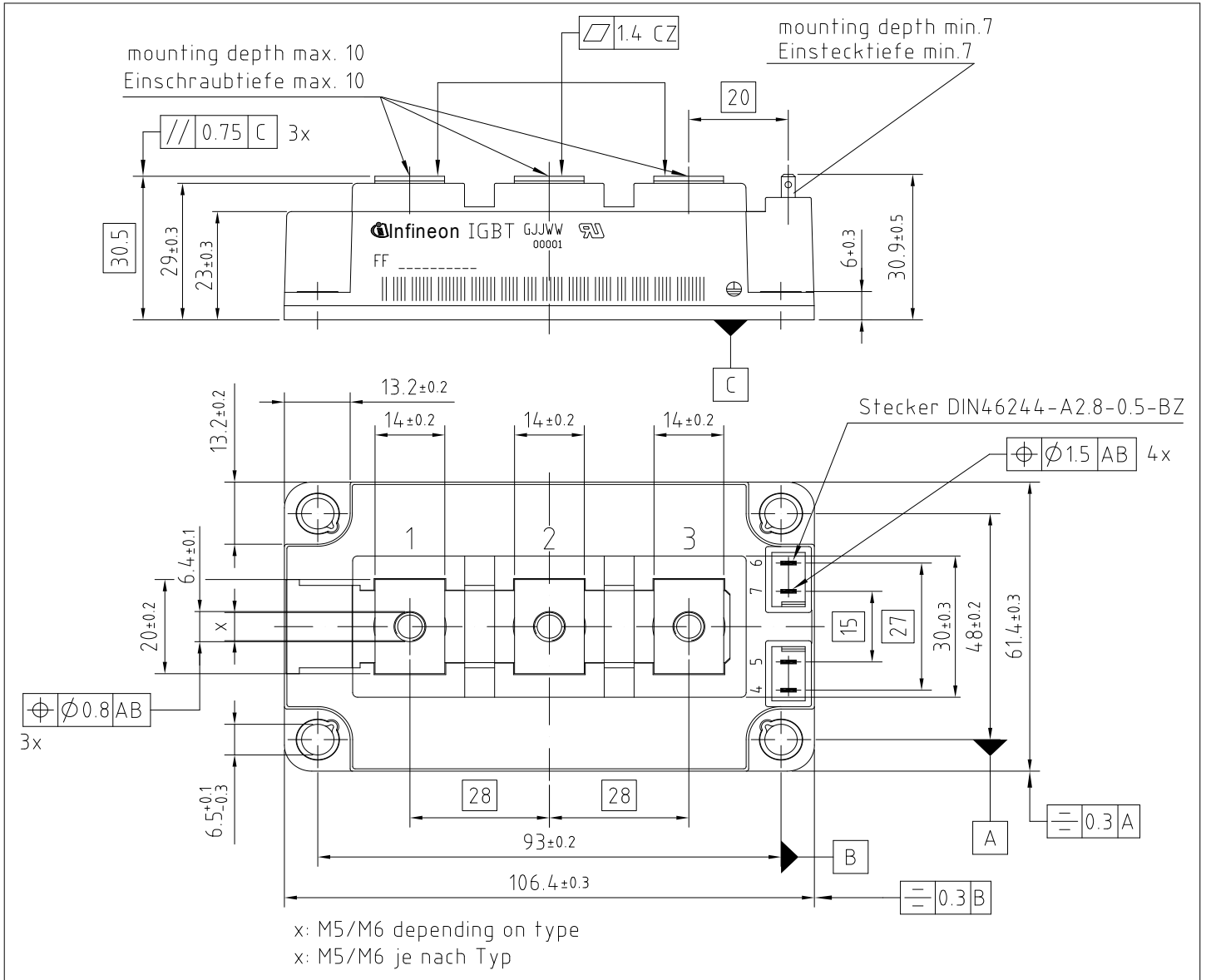



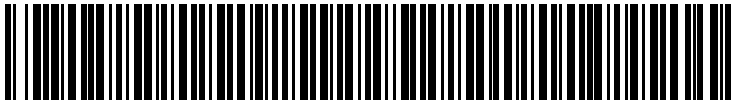
Figure 1

**6 Package outlines**



**Figure 2**

## 7 Module label code

<b>Module label code</b>			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i> Module serial number Module material number Production order number Date code (production year) Date code (production week)	<i>Digit</i> 1 - 5 6 - 11 12 - 19 20 - 21 22 - 23	<i>Example</i> 71549 142846 55054991 15 30
Example	<div style="display: flex; justify-content: space-around; align-items: center;"> <div style="text-align: center;">   71549142846550549911530 </div> <div style="text-align: center;">   71549142846550549911530 </div> </div>		

**Figure 3**

## Revision history

Document revision	Date of release	Description of changes
0.10	2023-03-17	Initial version

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**Email: [erratum@infineon.com](mailto:erratum@infineon.com)**

**Document reference**

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